



SPN6335

Dual N-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPN6335 is the Dual N-Channel enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. This high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where high-side switching , low in-line power loss, and resistance to transients are needed.

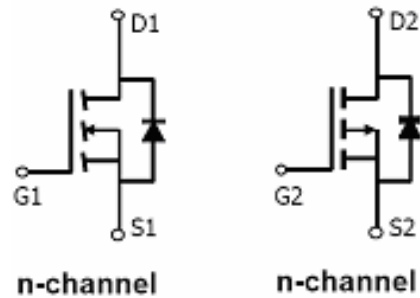
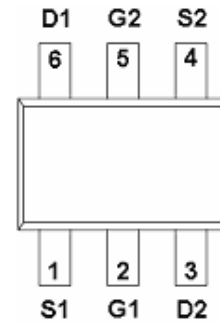
FEATURES

- ◆ N-Channel
 $20V/0.95A, R_{DS(ON)}=380m\Omega@V_{GS}=4.5V$
 $20V/0.75A, R_{DS(ON)}=450m\Omega@V_{GS}=2.5V$
 $20V/0.65A, R_{DS(ON)}=800m\Omega@V_{GS}=1.8V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-363 (SC-70-6L) package design

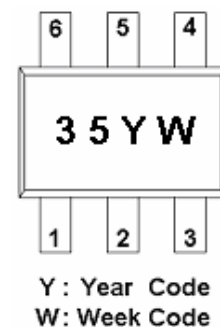
APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

PIN CONFIGURATION(SOT-363 / SC-70-6L)



PART MARKING





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PIN DESCRIPTION

Pin	Symbol	Description
1	G1	Gate 1
2	S2	Source 2
3	G2	Gate 2
4	D2	Drain 2
5	S1	Source 1
6	D1	Drain1

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN6335S36RG	SOT-363	35YW

- ※ Week Code : A ~ Z (1 ~ 26) ; a ~ z (27 ~ 52)
- ※ SPN6335S36RG : Tape Reel ; Pb – Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	20	V
Gate –Source Voltage	V _{GSS}	±12	V
Continuous Drain Current(T _J =150°C)	I _D	TA=25°C	1.2
		TA=80°C	0.9
Pulsed Drain Current	I _{DM}	4	A
Continuous Source Current(Diode Conduction)	I _S	0.6	A
Power Dissipation	P _D	TA=25°C	0.35
		TA=70°C	0.19
Operating Junction Temperature	T _J	-55/150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	T ≤ 10sec	360
		Steady State	400



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ELECTRICAL CHARACTERISTICS

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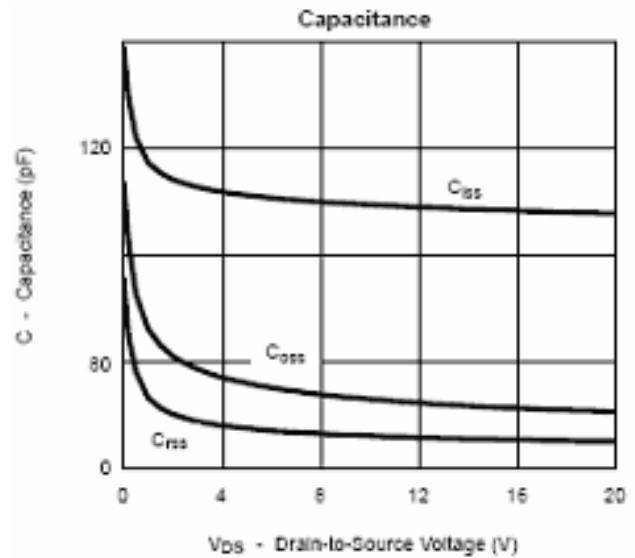
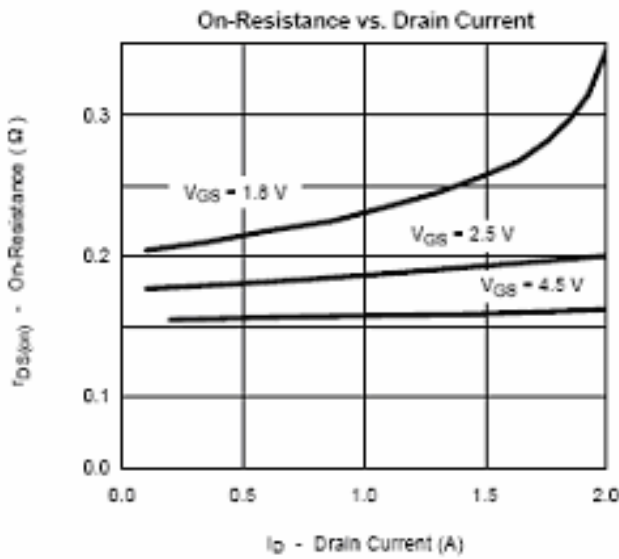
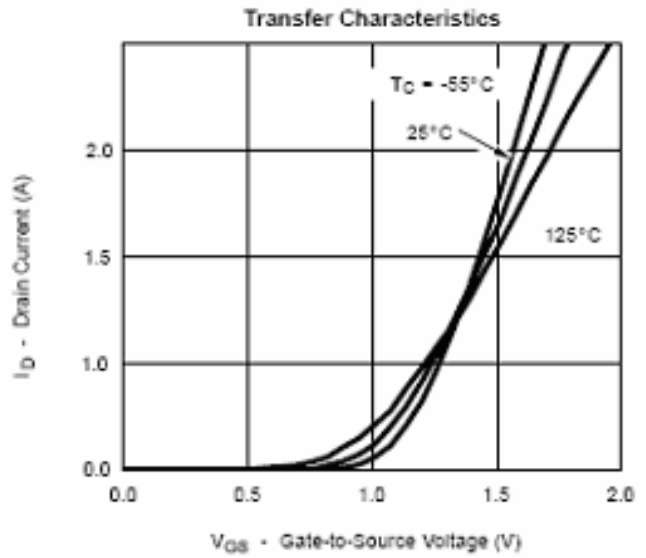
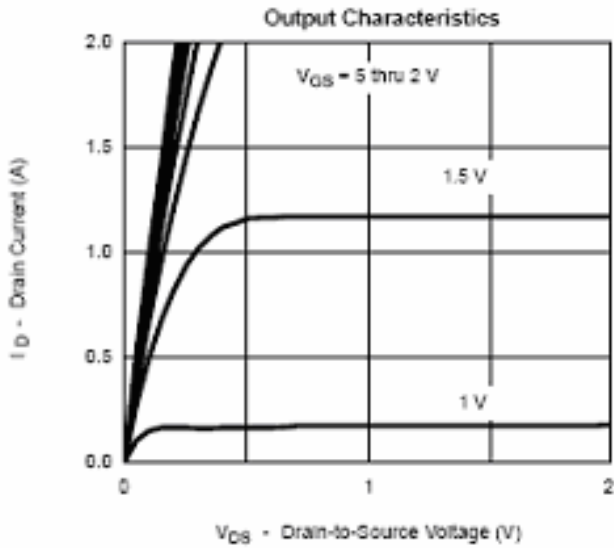
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D = 250uA	20			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	0.35		1.0	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20V, V _{GS} =0V			1	uA
		V _{DS} = 20V, V _{GS} =0V T _J =55°C			5	
On-State Drain Current	I _{D(on)}	V _{DS} ≥ 4.5V, V _{GS} =5V	2			A
Drain-Source On-Resistance	R _{DSS(on)}	V _{GS} =4.5V, I _D =0.95A		0.26	0.38	Ω
		V _{GS} =2.5V, I _D =0.75A		0.32	0.45	
		V _{GS} =1.8V, I _D =0.65A		0.42	0.80	
Forward Transconductance	g _{fs}	V _{DS} =10V, I _D =1.2A		2.6		S
Diode Forward Voltage	V _{SD}	I _S =0.5A, V _{GS} =0V		0.8	1.2	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =10V, V _{GS} =4.5V, I _D =0.7A		1.2	1.5	nC
Gate-Source Charge	Q _{gs}			0.2		
Gate-Drain Charge	Q _{gd}			0.3		
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V f=1MHz		110		pF
Output Capacitance	C _{oss}			34		
Reverse Transfer Capacitance	C _{rss}			16		
Turn-On Time	t _{d(on)}	V _{DD} =10V, R _L =10Ω , I _D =1.0A V _{GEN} =4.5V , R _G =6Ω		5	10	ns
	t _r			8	15	
Turn-Off Time	t _{d(off)}			10	18	
	t _f			1.2	2.8	



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TYPICAL CHARACTERISTICS

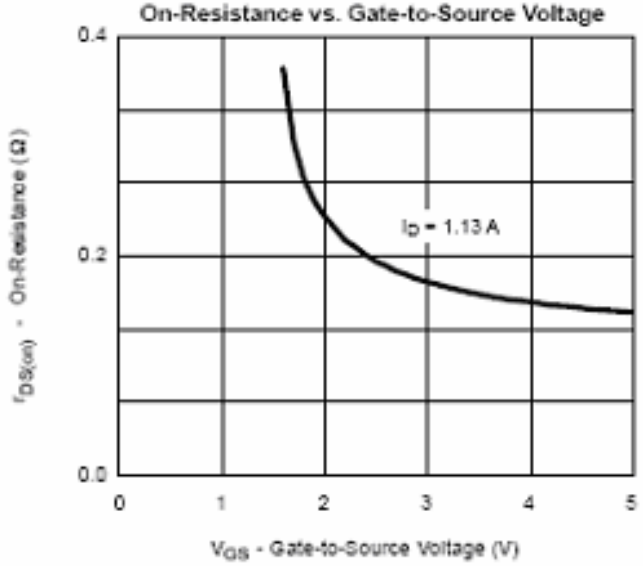
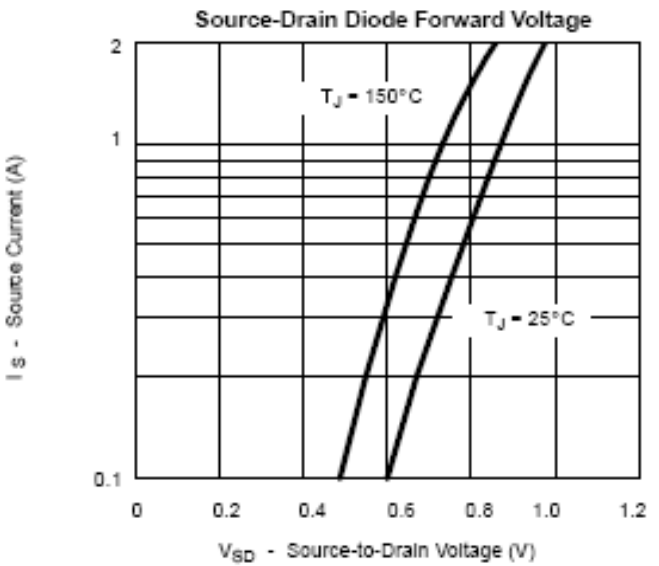
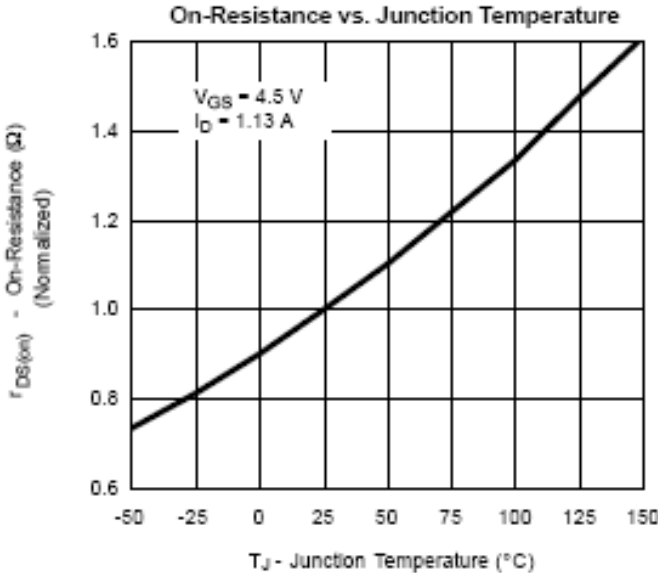
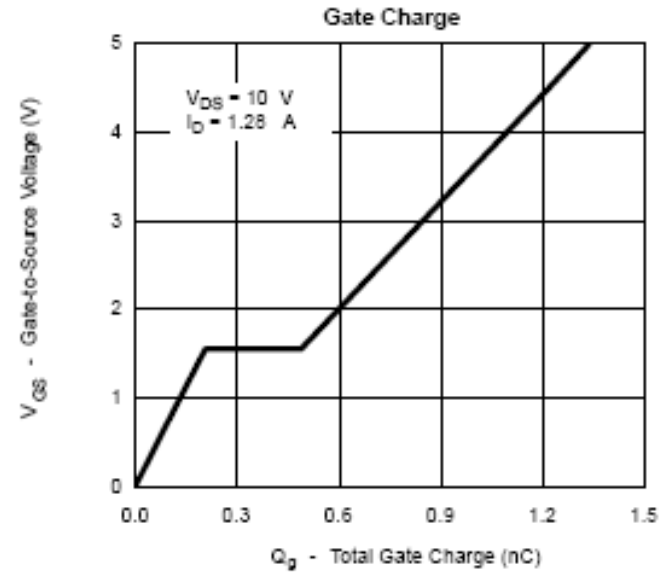




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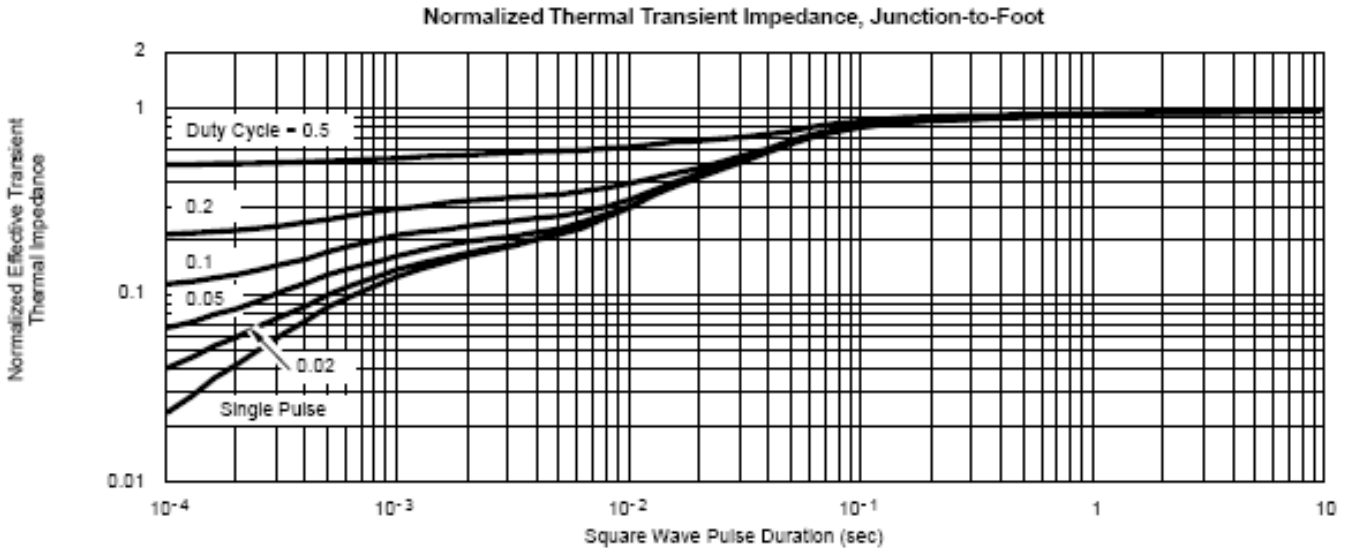
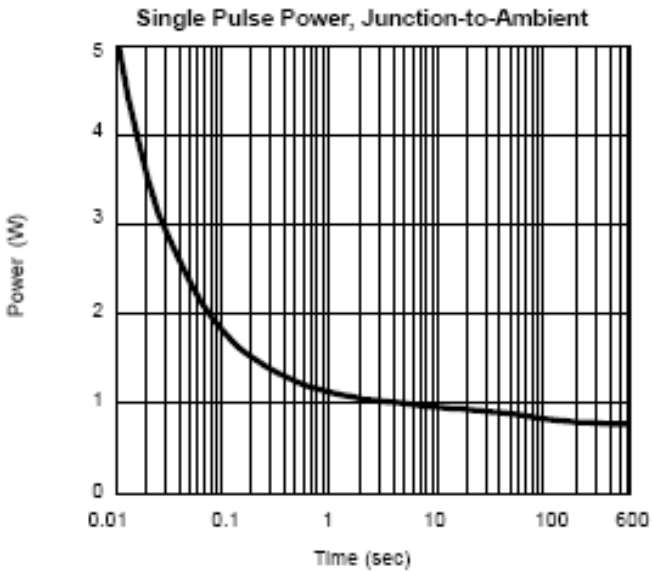
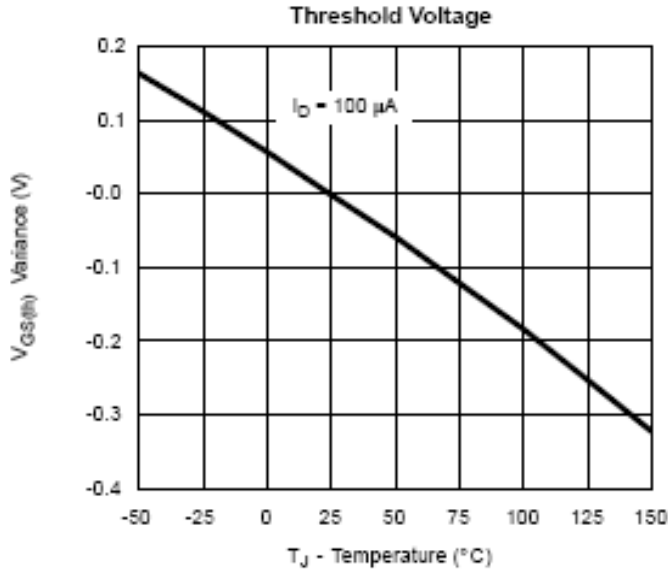




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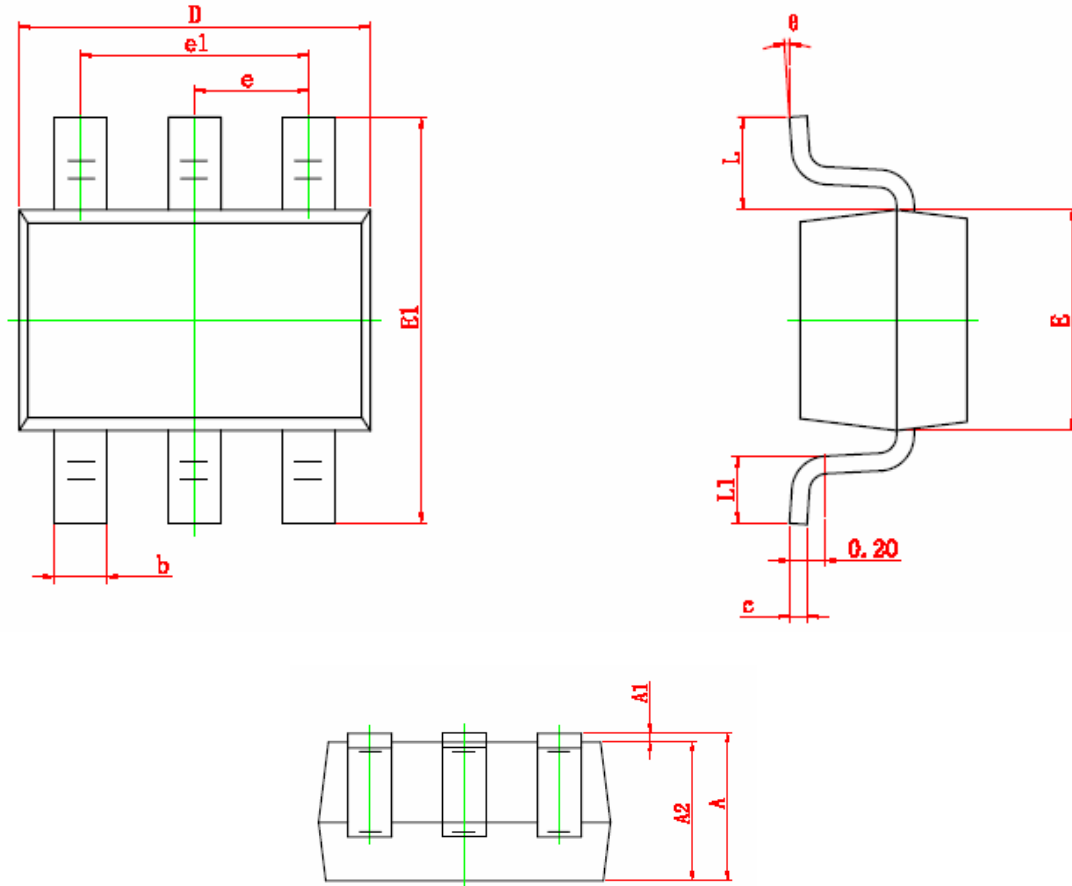




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SOT-363 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°



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SYNC Power Corporation

9F-5, No.3-2, Park Street

NanKang District (NKSP), Taipei, Taiwan 115

Phone: 886-2-2655-8178

Fax: 886-2-2655-8468

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